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BLL8H1214L-500; BLL8H1214LS-500 LDMOS L-band radar power transistor Rev. 3 — 1 September 2015

AMMPLEON

Product data sheet

Product profile 1.

1.1 General description

500 W LDMOS power transistor intended for L-band radar applications in the 1.2 GHz to 1.4 GHz range.

Test information Table 1.

Typical RF performance at T_{case} = 25 °C; t_p = 300 μ s; δ = 10 %; I_{Da} = 150 mA; in a class-AB production test circuit.

Test signal	f	V _{DS}	P _L	G _p	η_{D}	t _r	t _f
	(GHz)	(V)	(W)	(dB)	(%)	(ns)	(ns)
pulsed RF	1.2 to 1.4	50	500	17	50	20	6

1.2 Features and benefits

- Easy power control
- Integrated dual side ESD protection
- High flexibility with respect to pulse formats
- Excellent ruggedness
- High efficiency
- Excellent thermal stability
- Designed for broadband operation (1.2 GHz to 1.4 GHz)
- Internally matched for ease of use
- Compliant to Directive 2002/95/EC, regarding restriction of hazardous substances (RoHS)

1.3 Applications

 L-band power amplifiers for radar applications in the 1.2 GHz to 1.4 GHz frequency range

2. Pinning information

Table 2. Pinning

Pin	Description	Simplified out	line Graphic symbol
BLL8H12	14L-500 (SOT539A)		
1	drain1		
2	drain2	1 2	
3	gate1		<u></u>
4	gate2	3 4	3 - 5
5	source	[1]	4 7
			, ' <u> </u>
			2 sym117
BLL8H12	214LS-500 (SOT539B)		
1	drain1		
2	drain2	1 2	1
3	gate1		J 5
4	gate2	3 4	3——5
5	source	[1]	4 —
			"├─┐
			2 sym117
			-

^[1] Connected to flange.

3. Ordering information

Table 3. Ordering information

Type number	Packag	Package Package				
	Name	Description	Version			
BLL8H1214L-500	-	flanged balanced ceramic package; 2 mounting holes; 4 leads	SOT539A			
BLL8H1214LS-500	-	earless flanged balanced ceramic package; 4 leads	SOT539B			

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage		-	100	V
V_{GS}	gate-source voltage		-6	+13	V
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature	[1]	-	225	°C

Continuous use at maximum temperature will affect the reliability, for details refer to the on-line MTF calculator.

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Тур	Unit
Z _{th(j-c)}	transient thermal impedance from	T _{case} = 85 °C; P _L = 500 W		
	junction to case	t_p = 100 μ s; δ = 10 %	0.046	K/W
		t_p = 200 μ s; δ = 10 %	0.059	K/W
		t_p = 300 μ s; δ = 10 %	0.069	K/W
		t_p = 100 μ s; δ = 20 %	0.064	K/W

6. Characteristics

Table 6. DC characteristics

 $T_i = 25$ °C; per section unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{(BR)DSS}	drain-source breakdown voltage	$V_{GS} = 0 \text{ V}; I_D = 2.7 \text{ mA}$	100	-	-	V
V _{GS(th)}	gate-source threshold voltage	V _{DS} = 10 V; I _D = 270 mA	1.3	1.8	2.2	V
I _{DSS}	drain leakage current	V _{GS} = 0 V; V _{DS} = 50 V	-	-	1.4	μΑ
I _{DSX}	drain cut-off current	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $V_{DS} = 10 \text{ V}$	32	42	-	A
I _{GSS}	gate leakage current	V _{GS} = 11 V; V _{DS} = 0 V	-	-	140	nA
9 _{fs}	forward transconductance	V _{DS} = 10 V; I _D = 270 mA	1.7	3	-	S
R _{DS(on)}	drain-source on-state resistance	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $I_D = 9.5 \text{ A}$	-	100	164	mΩ

Table 7. RF characteristics

Test signal: pulsed RF; t_p = 300 μ s; δ = 10 %; RF performance at V_{DS} = 50 V; I_{Dq} = 150 mA; T_{case} = 25 °C; unless otherwise specified, in a class-AB production test circuit.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DS}	drain-source voltage	P _L = 500 W	-	-	50	V
Gp	power gain	P _L = 500 W	15	17	-	dB
RLin	input return loss	P _L = 500 W	-	-10	-	dB
P _{L(1dB)}	output power at 1 dB gain compression		-	600	-	W
η _D	drain efficiency	P _L = 500 W	45	50	-	%
P _{droop(pulse)}	pulse droop power	P _L = 500 W	-	0	0.3	dB
t _r	rise time	P _L = 500 W	-	20	50	ns
t _f	fall time	P _L = 500 W	-	6	50	ns

7. Test information

7.1 Ruggedness in class-AB operation

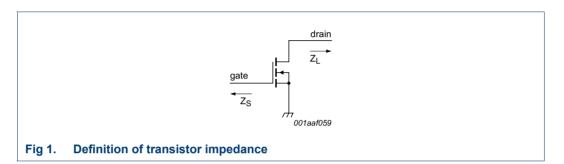
The BLL8H1214L-500 and BLL8H1214LS-500 are capable of withstanding a load mismatch corresponding to VSWR = 10 : 1 through all phases under the following conditions: V_{DS} = 50 V; I_{Dq} = 150 mA; P_{L} = 500 W; I_{p} = 300 μ s; δ = 10 %.

7.2 Impedance information

Table 8. Typical impedance

Typical values per section unless otherwise specified.

f	Z _S	Z _L
(GHz)	(Ω)	(Ω)
1.2	1.268 – j2.623	2.987 – j1.664
1.3	2.193 – j2.457	2.162 – j1.326
1.4	2.359 – j2.052	1.604 – j1.887



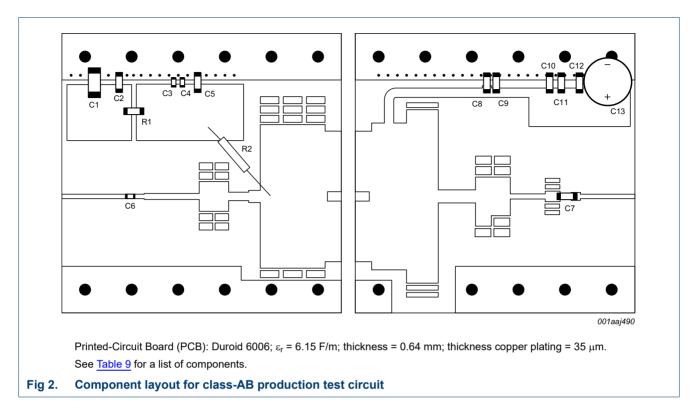
7.3 Test circuit

Table 9. List of components

For test circuit see Figure 2.

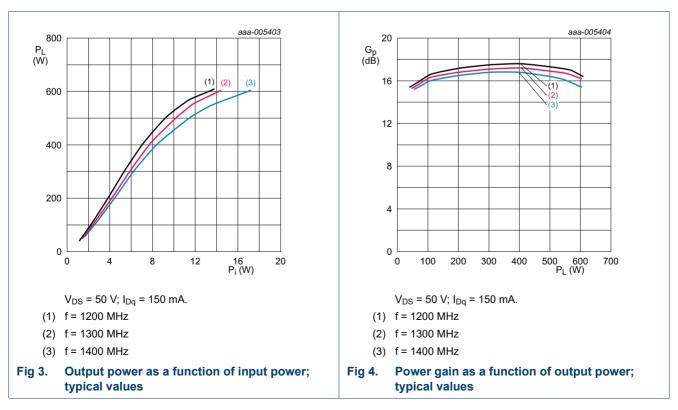
Component	Description	Value	Remarks
C1	multilayer ceramic chip capacitor	22 μF, 35 V	
C2	multilayer ceramic chip capacitor	51 pF [1]	
C3, C4	multilayer ceramic chip capacitor	100 pF [1]	
C5, C11, C12	multilayer ceramic chip capacitor	1 nF [2]	
C6	multilayer ceramic chip capacitor	47 pF [1]	
C7, C8, C10	multilayer ceramic chip capacitor	51 pF [3]	
C9	multilayer ceramic chip capacitor	100 pF [3]	
C13	electrolytic capacitor	10 μF, 63 V	
R1	SMD resistor	56 Ω	SMD 0603
R2	metal film resistor	51 Ω	

- [1] American Technical Ceramics type 100A or capacitor of same quality.
- [2] American Technical Ceramics type 100B or capacitor of same quality.
- [3] American Technical Ceramics type 800B or capacitor of same quality.

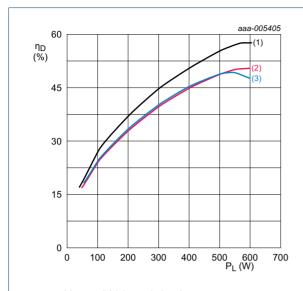


7.4 RF performance graphs

7.4.1 Performance curves measured with δ = 10 %, t_p = 300 μ s and T_h = 25 °C



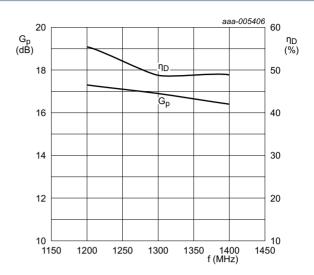
5 of 20



 $V_{DS} = 50 \text{ V}; I_{Dq} = 150 \text{ mA}.$

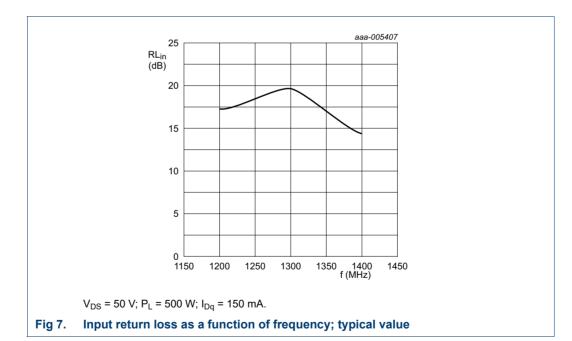
- (1) f = 1200 MHz
- (2) f = 1300 MHz
- (3) f = 1400 MHz

Fig 5. Drain efficiency as a function of output power; typical values

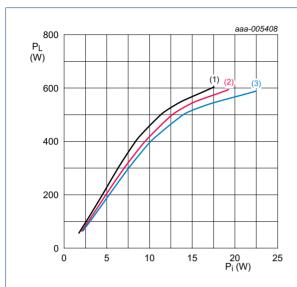


 V_{DS} = 50 V; P_{L} = 500 W; I_{Dq} = 150 mA.

Fig 6. Power gain and drain efficiency as function of frequency; typical values



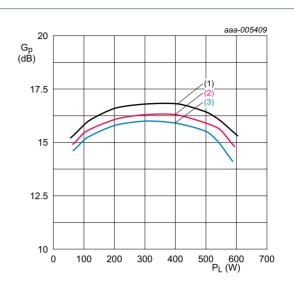
7.4.2 Performance curves measured with δ = 10 %, t_p = 300 μ s and T_h = 65 °C



 $V_{DS} = 50 \text{ V}; I_{Dq} = 150 \text{ mA}.$

- (1) f = 1200 MHz
- (2) f = 1300 MHz
- (3) f = 1400 MHz

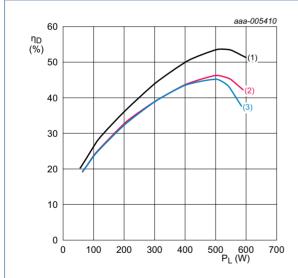
Fig 8. Output power as a function of input power; typical values



 $V_{DS} = 50 \text{ V}; I_{Dq} = 150 \text{ mA}.$

- (1) f = 1200 MHz
- (2) f = 1300 MHz
- (3) f = 1400 MHz

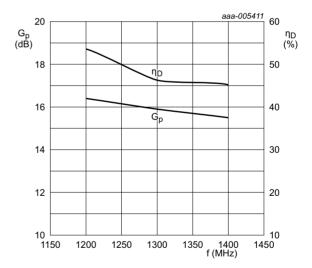
Fig 9. Power gain as a function of output power; typical values



 $V_{DS} = 50 \text{ V}; I_{Dq} = 100 \text{ mA}.$

- (1) f = 1200 MHz
- (2) f = 1300 MHz
- (3) f = 1400 MHz

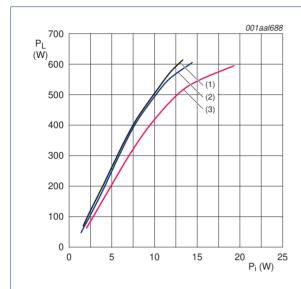
Fig 10. Drain efficiency as a function of output power; typical values



 $V_{DS} = 50 \text{ V}$; $P_L = 500 \text{ W}$; $I_{Dq} = 100 \text{ mA}$.

Fig 11. Power gain and drain efficiency as function of frequency; typical values

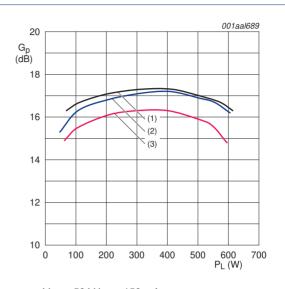
7.4.3 Performance curves measured with δ = 10 %, t_p = 300 μ s and f = 1300 MHz



 $V_{DS} = 50 \text{ V}; I_{Dq} = 150 \text{ mA}.$

- (1) $T_h = -40 \, ^{\circ}C$
- (2) $T_h = +25 \, ^{\circ}C$
- (3) $T_h = +65 \, ^{\circ}C$

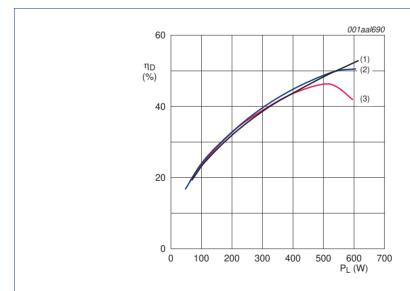
Fig 12. Output power as a function of input power; typical values



 $V_{DS} = 50 \text{ V;} I_{Dq} = 150 \text{ mA}.$

- (1) $T_h = -40 \, ^{\circ}C$
- (2) $T_h = +25 \, ^{\circ}C$
- (3) $T_h = +65 \, ^{\circ}C$

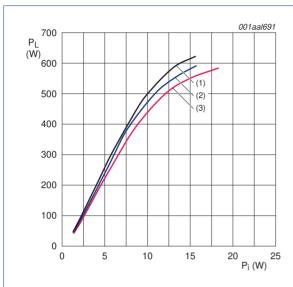
Fig 13. Power gain as a function of output power; typical values



- (1) $T_h = -40 \, ^{\circ}C$
- (2) $T_h = +25 \, ^{\circ}C$
- (3) $T_h = +65 \, ^{\circ}C$

Fig 14. Drain efficiency as a function of output power; typical values

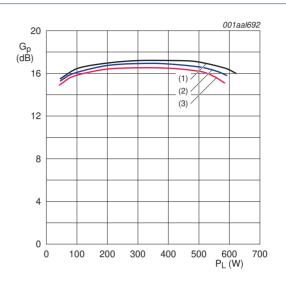
7.4.4 Performance curves measured with δ = 20 %, t_p = 500 μ s and T_h = 25 °C



 $V_{DS} = 50 \text{ V}; I_{Dq} = 150 \text{ mA}.$

- (1) f = 1200 MHz
- (2) f = 1300 MHz
- (3) f = 1400 MHz

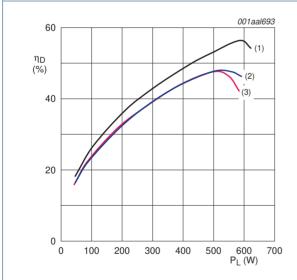
Fig 15. Output power as a function of input power; typical values



 $V_{DS} = 50 \text{ V}; I_{Dq} = 150 \text{ mA}.$

- (1) f = 1200 MHz
- (2) f = 1300 MHz
- (3) f = 1400 MHz

Fig 16. Power gain as a function of output power; typical values



 $V_{DS} = 50 \text{ V}; I_{Dq} = 150 \text{ mA}.$

- (1) f = 1200 MHz
- (2) f = 1300 MHz
- (3) f = 1400 MHz

Fig 17. Drain efficiency as a function of output power; typical values

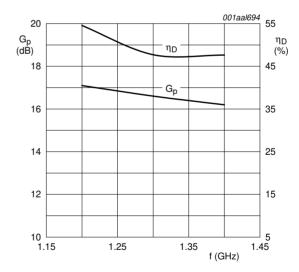
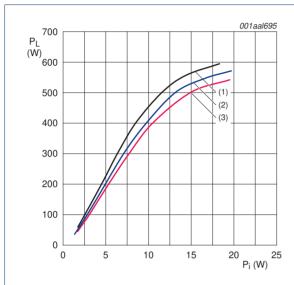


Fig 18. Power gain and drain efficiency as function of frequency; typical values

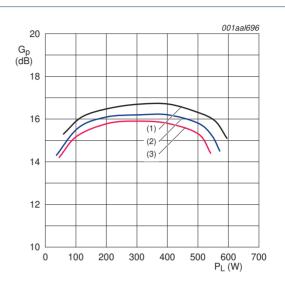
7.4.5 Performance curves measured with δ = 20 %, t_p = 500 μ s and T_h = 65 °C



 $V_{DS} = 50 \text{ V}; I_{Dq} = 150 \text{ mA}.$

- (1) f = 1200 MHz
- (2) f = 1300 MHz
- (3) f = 1400 MHz

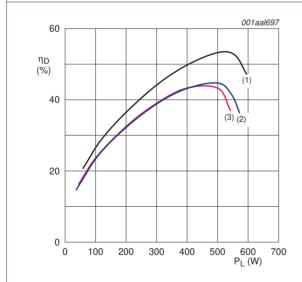
Fig 19. Output power as a function of input power; typical values



 $V_{DS} = 50 \text{ V}; I_{Dq} = 150 \text{ mA}.$

- (1) f = 1200 MHz
- (2) f = 1300 MHz
- (3) f = 1400 MHz

Fig 20. Power gain as a function of output power; typical values



 $V_{DS} = 50 \text{ V}; I_{Dq} = 150 \text{ mA}.$

- (1) f = 1200 MHz
- (2) f = 1300 MHz
- (3) f = 1400 MHz

Fig 21. Drain efficiency as a function of output power; typical values

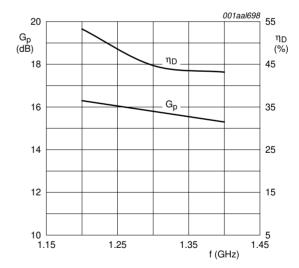
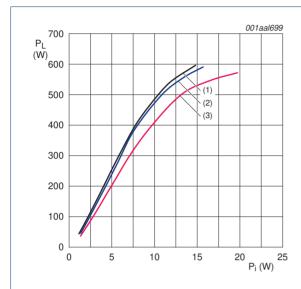


Fig 22. Power gain and drain efficiency as function of frequency; typical values

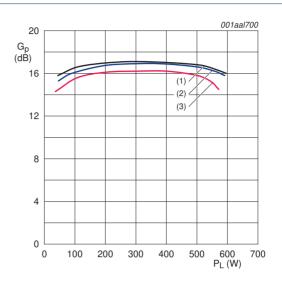
7.4.6 Performance curves measured with δ = 20 %, t_p = 500 μ s and f = 1300 MHz



 $V_{DS} = 50 \text{ V}; I_{Dq} = 150 \text{ mA}.$

- (1) $T_h = -40 \, ^{\circ}C$
- (2) $T_h = +25 \, ^{\circ}C$
- (3) $T_h = +65 \, ^{\circ}C$

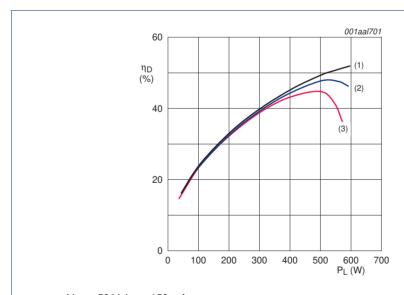
Fig 23. Output power as a function of input power; typical values



 $V_{DS} = 50 \text{ V}; I_{Dq} = 150 \text{ mA}.$

- (1) $T_h = -40 \, ^{\circ}C$
- (2) $T_h = +25 \, ^{\circ}C$
- (3) $T_h = +65 \, ^{\circ}C$

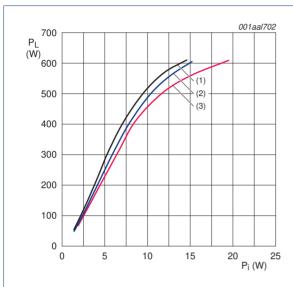
Fig 24. Power gain as a function of output power; typical values



- (1) $T_h = -40 \, ^{\circ}C$
- (2) $T_h = +25 \, ^{\circ}C$
- (3) $T_h = +65 \, ^{\circ}C$

Fig 25. Drain efficiency as a function of output power; typical values

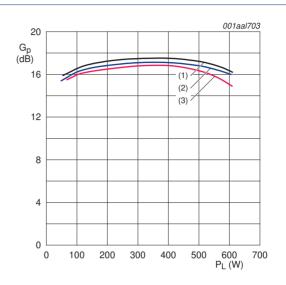
7.4.7 Performance curves measured with δ = 10 %, t_p = 1 ms and T_h = 25 °C



 $V_{DS} = 50 \text{ V}; I_{Dq} = 150 \text{ mA}.$

- (1) f = 1200 MHz
- (2) f = 1300 MHz
- (3) f = 1400 MHz

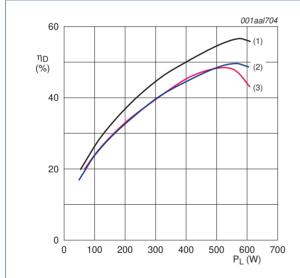
Fig 26. Output power as a function of input power; typical values



 $V_{DS} = 50 \text{ V}; I_{Dq} = 150 \text{ mA}.$

- (1) f = 1200 MHz
- (2) f = 1300 MHz
- (3) f = 1400 MHz

Fig 27. Power gain as a function of output power; typical values



 $V_{DS} = 50 \text{ V}; I_{Dq} = 150 \text{ mA}.$

- (1) f = 1200 MHz
- (2) f = 1300 MHz
- (3) f = 1400 MHz

Fig 28. Drain efficiency as a function of output power; typical values

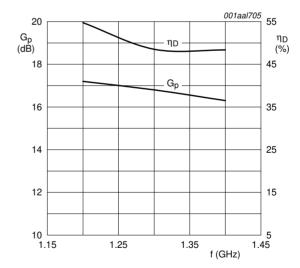
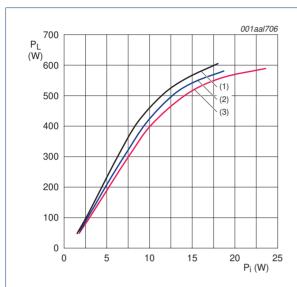


Fig 29. Power gain and drain efficiency as function of frequency; typical values

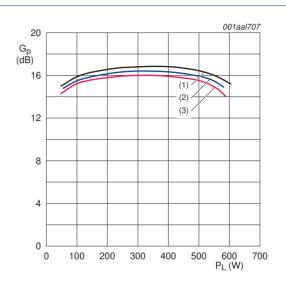
7.4.8 Performance curves measured with δ = 10 %, t_p = 1 ms and T_h = 65 °C



 $V_{DS} = 50 \text{ V}; I_{Dq} = 150 \text{ mA}.$

- (1) f = 1200 MHz
- (2) f = 1300 MHz
- (3) f = 1400 MHz

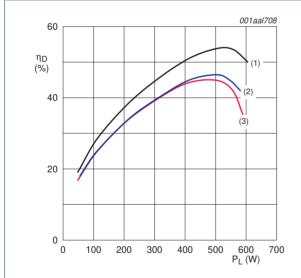
Fig 30. Output power as a function of input power; typical values



 $V_{DS} = 50 \text{ V}; I_{Dq} = 150 \text{ mA}.$

- (1) f = 1200 MHz
- (2) f = 1300 MHz
- (3) f = 1400 MHz

Fig 31. Power gain as a function of output power; typical values



 $V_{DS} = 50 \text{ V}; I_{Dq} = 150 \text{ mA}.$

- (1) f = 1200 MHz
- (2) f = 1300 MHz
- (3) f = 1400 MHz

Fig 32. Drain efficiency as a function of output power; typical values

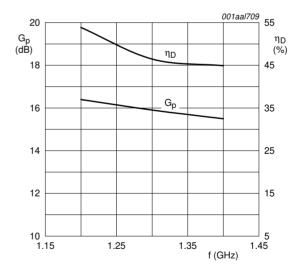
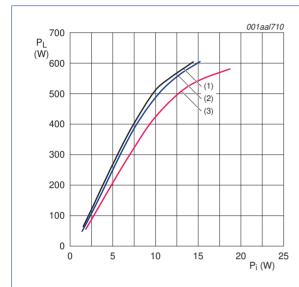


Fig 33. Power gain and drain efficiency as function of frequency; typical values

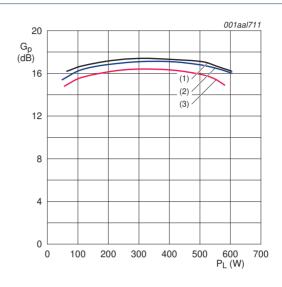
7.4.9 Performance curves measured with δ = 10 %, t_p = 1 ms and f = 1300 MHz



 $V_{DS} = 50 \text{ V}; I_{Dq} = 150 \text{ mA}.$

- (1) $T_h = -40 \, ^{\circ}C$
- (2) $T_h = +25 \, ^{\circ}C$
- (3) $T_h = +65 \,^{\circ}C$

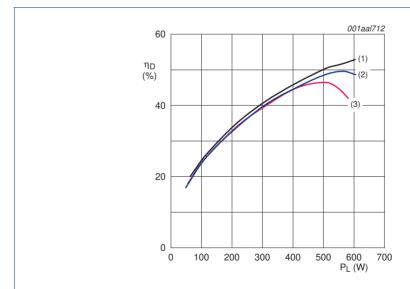
Fig 34. Output power as a function of input power; typical values



 $V_{DS} = 50 \text{ V}; I_{Dq} = 150 \text{ mA}.$

- (1) $T_h = -40 \, ^{\circ}C$
- (2) $T_h = +25 \, ^{\circ}C$
- (3) $T_h = +65 \, ^{\circ}C$

Fig 35. Power gain as a function of output power; typical values



- (1) $T_h = -40 \, ^{\circ}C$
- (2) $T_h = +25 \, ^{\circ}C$
- (3) $T_h = +65 \, ^{\circ}C$

Fig 36. Drain efficiency as a function of output power; typical values

8. Package outline

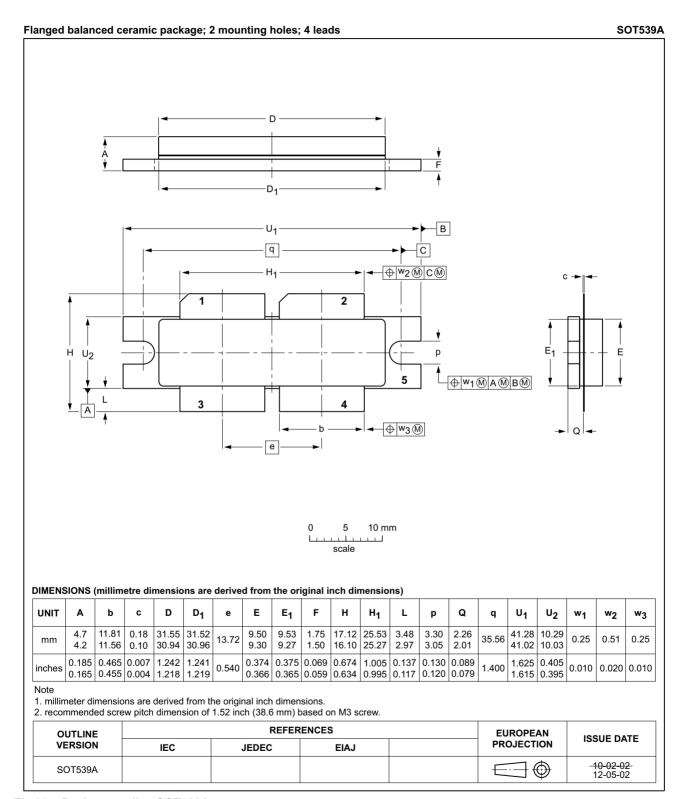


Fig 37. Package outline SOT539A

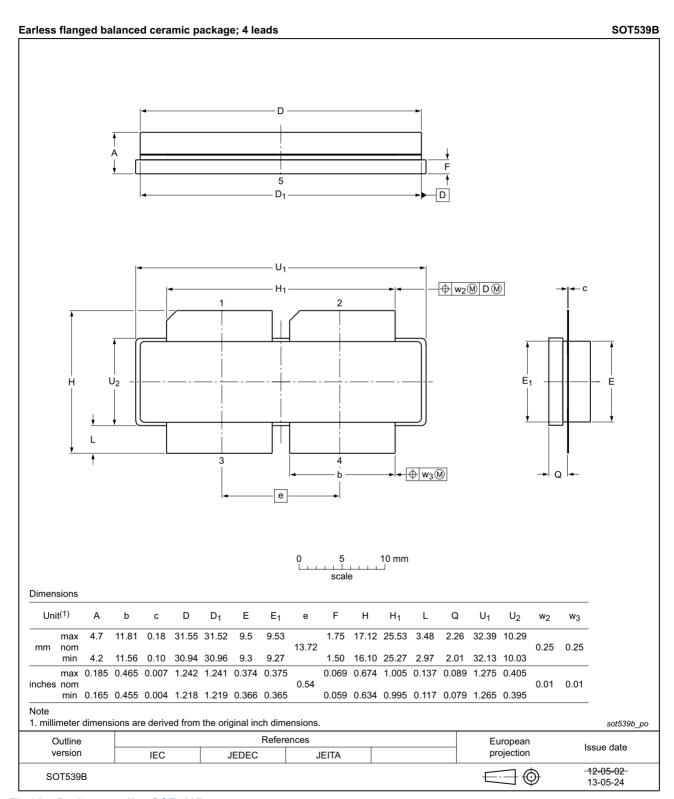


Fig 38. Package outline SOT539B

9. Handling information

CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the *ANSI/ESD S20.20*, *IEC/ST 61340-5*, *JESD625-A* or equivalent standards.

10. Abbreviations

Table 10. Abbreviations

Acronym	Description	
ESD	ElectroStatic Discharge	
L-band	ong wave Band	
LDMOS	Laterally Diffused Metal-Oxide Semiconductor	
MTF	Median Time to Failure	
SMD	Surface Mounted Device	
VSWR	Voltage Standing-Wave Ratio	

11. Revision history

Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes	
BLL8H1214L-500_1214LS-500 #3	20150901	Product data sheet	-	BLL8H1214L-500_1214LS-500 #2	
Modifications:	 The format of this document has been redesigned to comply with the new identity guidelines of Ampleon. Legal texts have been adapted to the new company name where appropriate. 				
BLL8H1214L-500_1214LS-500 #2	20150209	Product data sheet	-	BLL8H1214L-500_1214LS-500 #1	
BLL8H1214L-500_1214LS-500 #1	20140930	Objective data sheet	-	-	

12. Legal information

12.1 Data sheet status

Document status[1][2]	Product status[3]	Definition	
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.	
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.	
Product [short] data sheet	Production	This document contains the product specification.	

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.ampleon.com.

12.2 Definitions

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